

## Half-metallic and magnetic semiconductor natures in CdO monolayer induced by acceptor impurities

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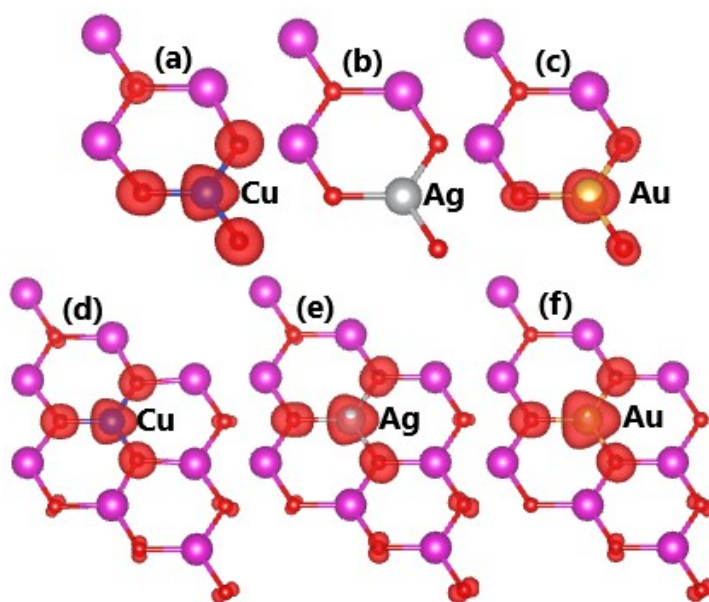


Figure S1: Spin density (Iso-surface value:  $0.004 e / \text{\AA}^3$ ) in CdO monolayer doped with 25%-11.11% of (a-d) Cu, (b-e) Ag, and (c-f) Au.

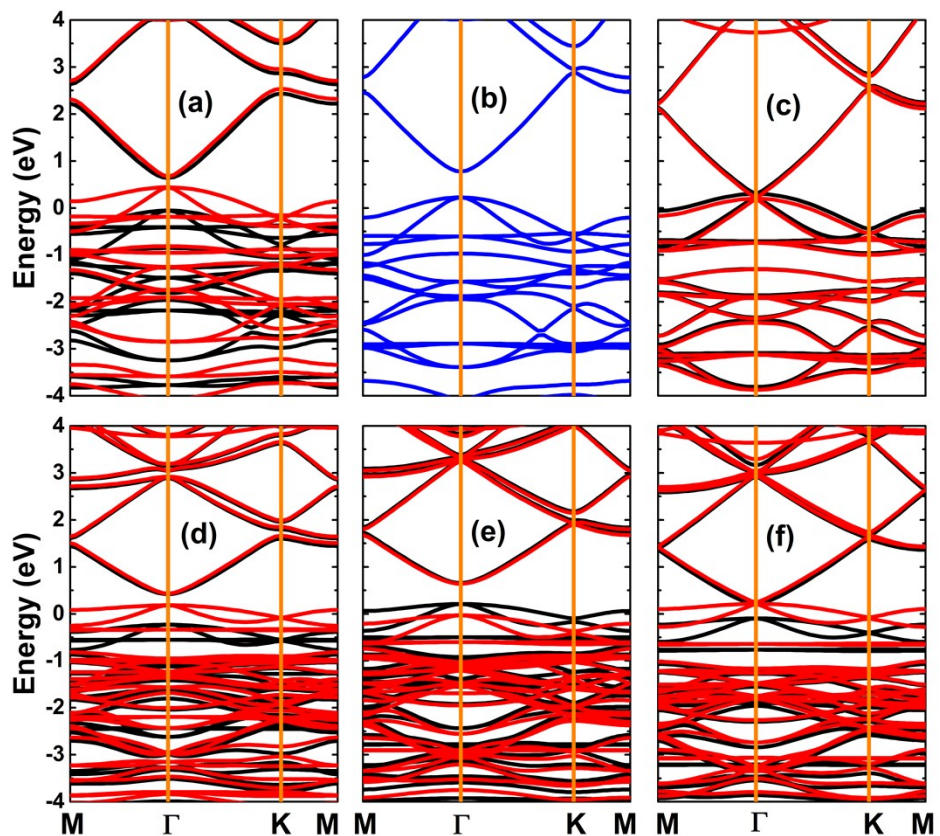


Figure S2: Spin-polarized band structure (Black curve: spin-up; Red curve: spin-down; Blue curve: non-spin-polarization; The Fermi level is set to 0 eV) of CdO monolayer doped with 25%-11.11% of (a-d) Cu, (b-e) Ag, and (c-f) Au.

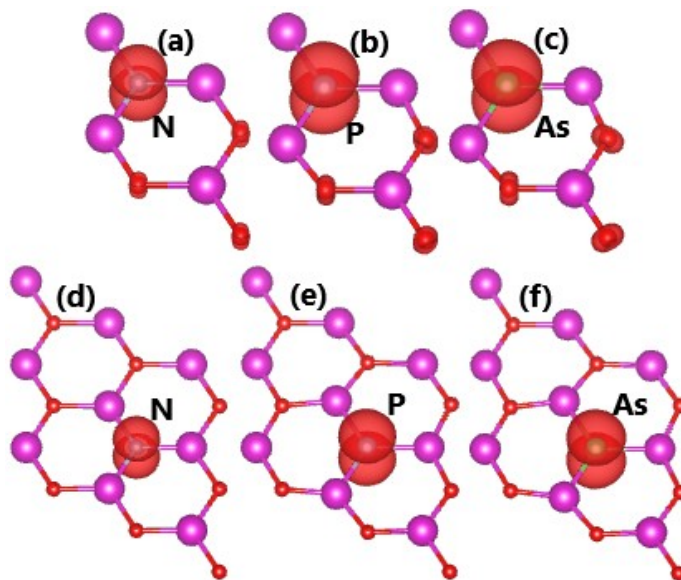


Figure S3: Spin density (Iso-surface value:  $0.004 e/\text{\AA}^3$ ) in CdO monolayer doped with 25%-11.11% of (a-d) N, (b-e) P, and (c-f) As.

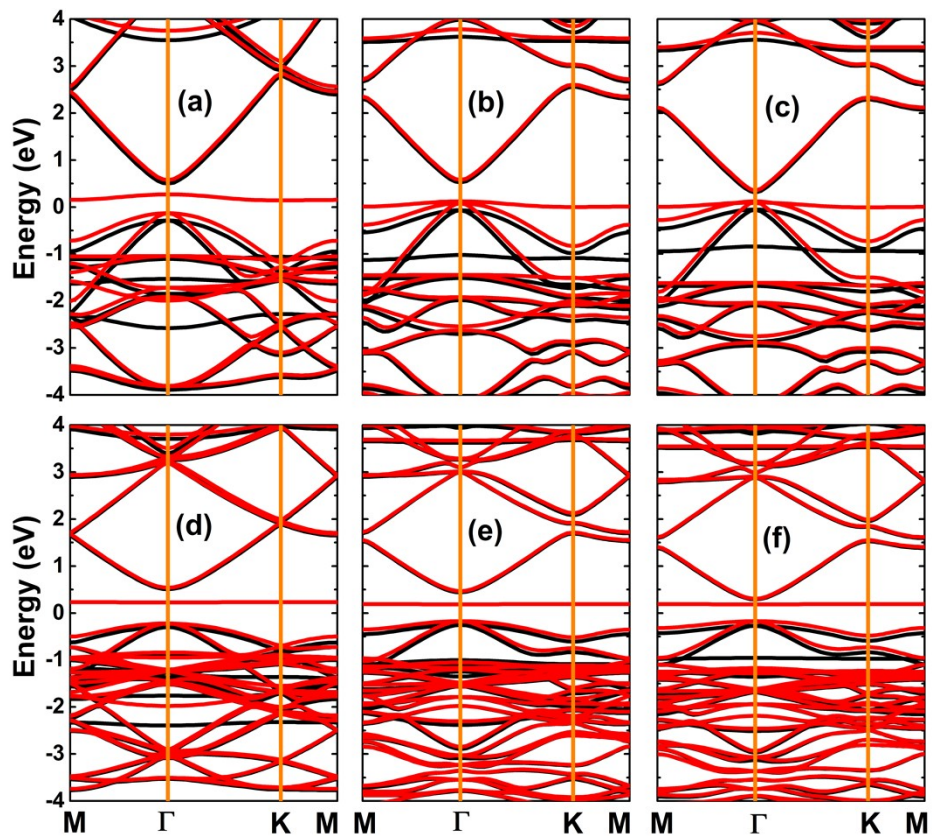


Figure S4: Spin-polarized band structure (Black curve: spin-up; Red curve: spin-down; Blue curve: non-spin-polarization; The Fermi level is set to 0 eV) of CdO monolayer doped with 25%-11.11% of (a-d) N, (b-e) P, and (c-f) As.